



Washington University in St. Louis Etching Capabilities

Nathan Reed
nreed@wustl.edu





Oxford Plasmalab System 100- ICP180

Process chamber: ICP180 for **4" wafers**

Chamber heating: Yes

Lower electrode type: Clamped

ICP source: ICP180 2000W

Lower electrode power supply/automatch: 600W + vacuum cap automatch

Vacuum gauges: 100mT CM gauge + Penning

Pumping pipework/APC valve: 160mm + 200mm VAT

Toxic gas lines/MFCs: **20 NF₃, 100 BCl₃, 100 Cl₂**

Non-toxic gas lines/MFCs: **100CF₄, 100 O₂, 100 CHF₃, 100 Ar, 100 N₂, 100 He, 100SF₆**

Loadlock: Single wafer

Heater/chiller: Yes 10 to 90°C

Endpoint Detectors: **Integrated Laser Interferometer End Point Detector**

Chamber Pumps: Aclatel 500l/s magnetic turbo pump backed by Alcatel 2063 Wet Pump

Loadlock Pumps: From Process backing

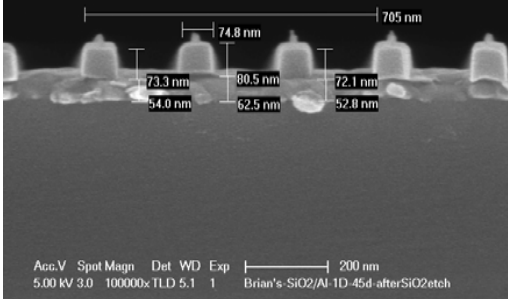


Gas	Application
CF ₄	
SF ₆	Si
CHF ₃	SiO ₂
NF ₃	Si, SiC
BCl ₃	Al
Cl ₂	III-V, Al
HBr	III-V
Ar	additive
O ₂	polymer
He	cooling
CH ₄	III-V
H ₂	III-V



Aluminum Etching

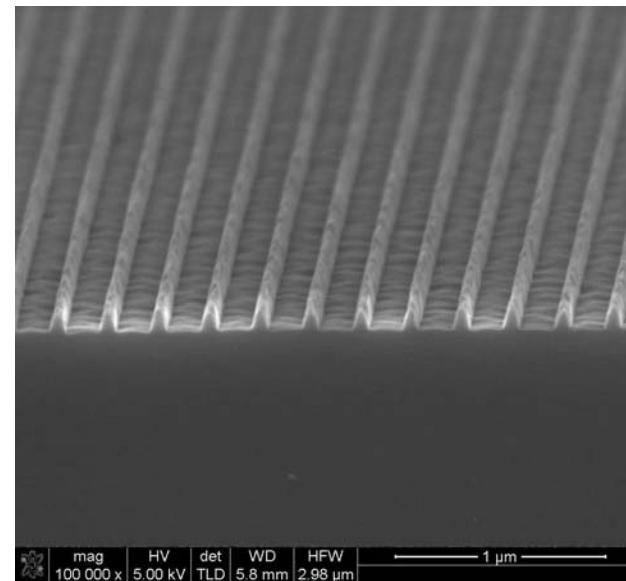
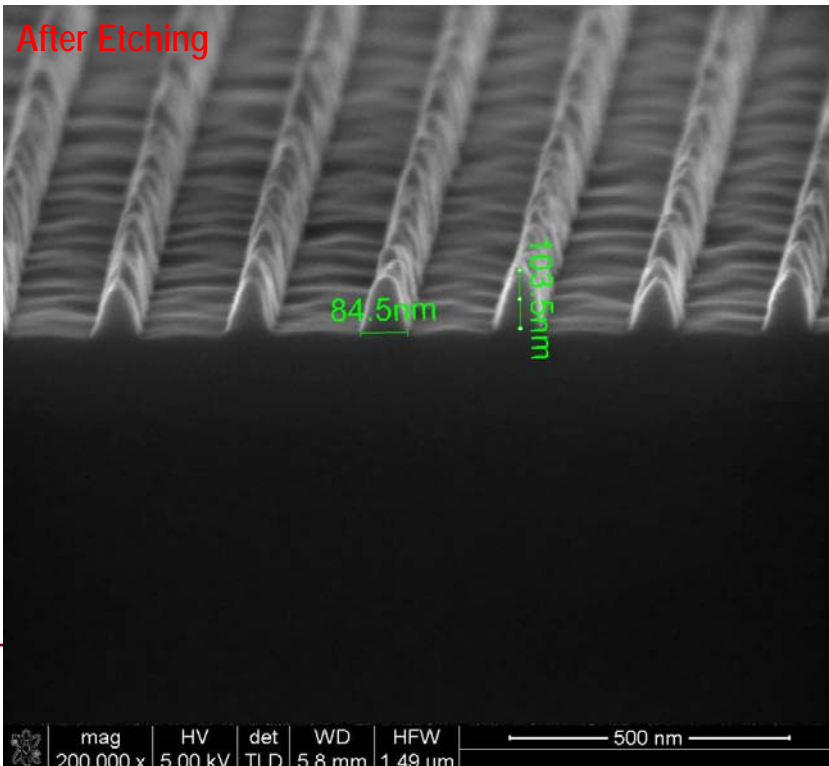
Original Sample



Sample: Aluminum film (80-nm thick) on silicon wafer, masked with SiO₂ patterns (75-nm lines, 70-nm thick)

Recipe: 20sccm Cl₂, 5mTorr, 200W, 1000W, 10Torr He, 80C, 10sec
20sccm HBr, 2mTorr, 100W, 800W, 10Torr He, 80C, 40sec

After Etching

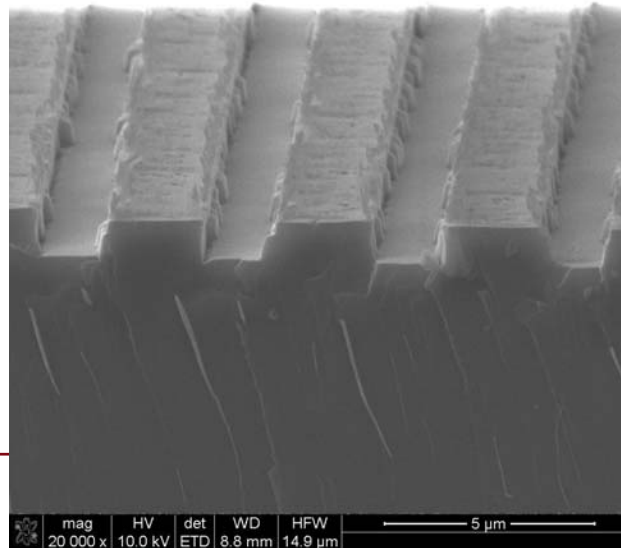
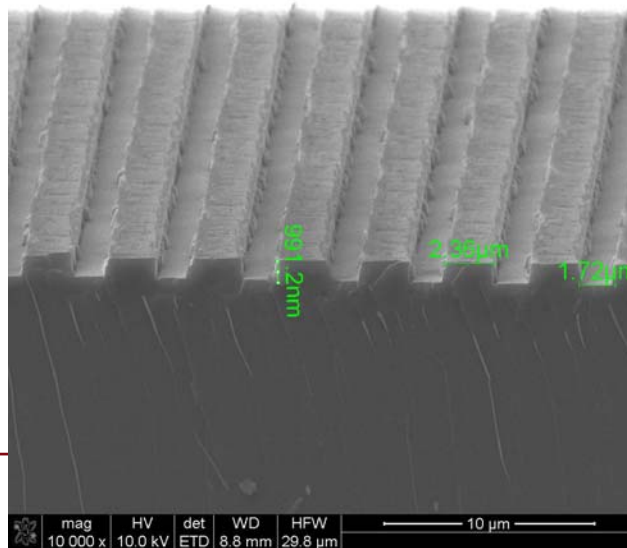
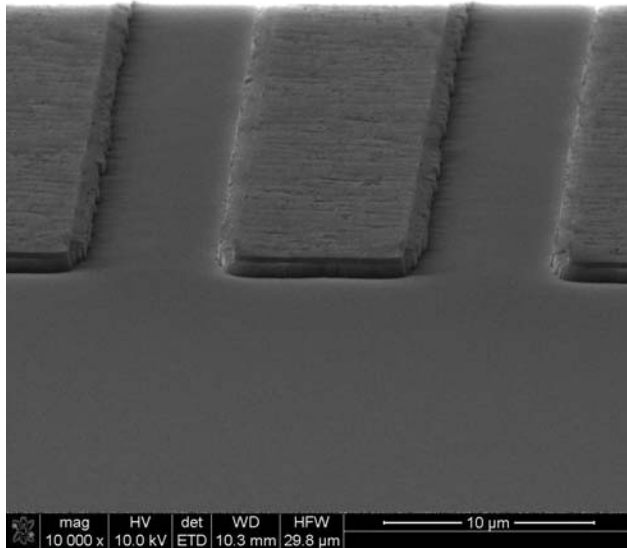


Silicon Etching

Sample: silicon wafer, masked with AZ5214 patterns (2-um lines, 10-um lines, etc.)

Recipe: 50sccm HBr, 7mTorr, 50W, 750W, 10Torr He, 50C, 5min

Note: the roughness of silicon ribbon edges was transferred from AZ patterns.





GaAs Etching

Sample: GaAs wafer, masked with PMMA patterns (e-beam lithography)

Recipe: 50sccm BrCl₃, 5mTorr, 200W, 600W, 10Torr He, 10C, 30sec

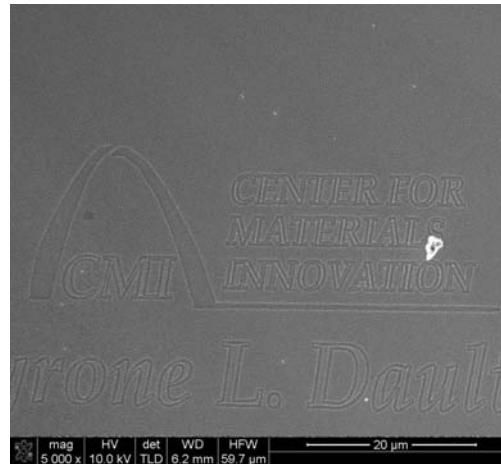
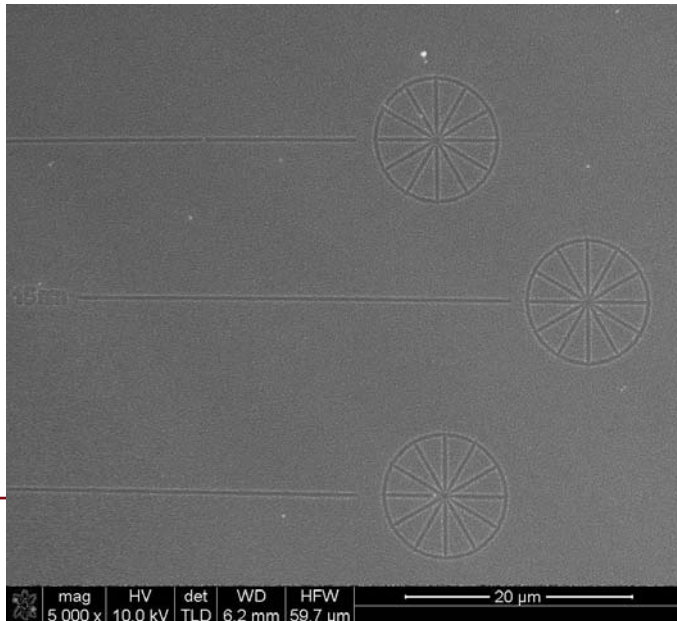
30sccm BCl₃, 80sccm Cl₂, 7mTorr, 115W, 600W, 10mTorr He, 10C, 15sec

Etch rate: ~ 1 μ m/min

Selectivity to resist: ~ 5-15:1

Selectivity to oxide: ~ 15-30:1

Profile: Anisotropic





Chamber Conditioning

- 15 minute O₂ after each run
- 1 hour clean each month
- User discretion for additional conditioning based on previous runs





Future Plans

- No new tool acquisitions
- Development of new baselines, recipes, and SOPs
- Development of new maintenance strategies





Questions?

nano.wustl.edu

nreed@wustl.edu

